In the Claims

Please replace all prior versions, and listings, of claims in the application with the following list of claims:

Applicant submits below a complete listing of the current claims, including marked-up claims with insertions indicated by underlining and deletions indicated by strikeouts and/or double bracketing. This listing of claims will replace all prior versions, and listings, of claims in the application:

Please cancel claims 4-8 without prejudice.

CLAIMS

1. (Currently amended) An integrated circuit comprising a buried layer of determined conductivity type in a plane substantially parallel to ~~the~~ a plane of a main circuit surface, wherein a median portion of said buried layer is filled with a metal-type material.

2. (Original) The integrated circuit of claim 1, wherein the buried layer is a sub-collector layer of a bipolar transistor.

3. (Original) The integrated circuit of claim 1, wherein the metal-type material is titanium nitride.

4. (Cancelled)

5. (Cancelled)

6. (Cancelled)

7. (Cancelled)

8. (Cancelled)

9. (New) An integrated circuit comprising a buried layer of determined conductivity type disposed in a plane substantially parallel to a surface of the integrated circuit, wherein at least a portion of the buried layer includes a metal-type material.

10. (New) The integrated circuit of claim 9, wherein the metal-type material forms a core of the buried layer.

11. (New) The integrated circuit of claim 1, wherein the buried layer is a sub-collector layer of a bipolar transistor.

12. (New) The integrated circuit of claim 1, wherein the metal-type material is chosen from the group consisting of conductive oxides, metal silicides, titanium nitride, tantalum nitride, or copper.